



Features

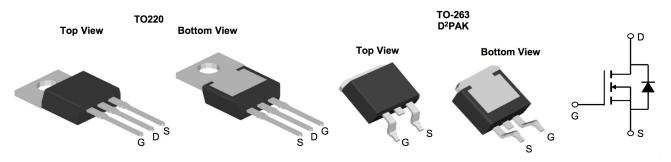
- 100V/195A $R_{DS (ON)} = 3.2 \text{m}\Omega(\text{Typ.})@V_{GS} = 10V$
- Advanced HEFE
 Technology
- Ultra Low On-Resistanc
- Excellent $_{g}xR_{DS(on)}$ Product
- 100% avalanche testedh t t d
- 175°C Operating Temperatur
- Lead Free and Green Devices Available (RoHS Compliant

Applications

- Motor Drive
- Uninterruptible Power Supplie
- DC/DC converte
- General Purpose Application



• Pin Configurations



● Absolute Maximum Ratings @T_A=25°C unless otherwise noted

Pa	Symbol	Ratings	Unit	
Drain-Source Voltage	$V_{ extsf{DSS}}$	100	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current G	Tc=25°C	1	205	Δ.
Continuous Drain Current G	Tc=100°C	I _D	120	A
Pulsed Drain Current c	I _{DM}	425	A	
Continuous Drain Current	T _A =25°C		29	Δ.
Continuous Drain Current	T _A =70°C	I _{DSM}	23	A
Avalanche Current c	I _{AS}	77	A	
Avalanche energy L=0.1mH c		EAS	296	mJ
Vos Spike	10µs	VSPIKE	120	V



Electrical Characteristics (T_C=25°C Unless Otherwise Noted)

Symbol	Parameter			11!4		
		Test Condition	Min.	Тур.	Max.	Unit
Static Chara	acteristics		•	•		
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100			V
	Zoro Cata Valtaga Drain Current	V _{DS} =100V, V _{GS} =0V			1	μΑ
I _{DSS} Z	Zero Gate Voltage Drain Current	T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2		4	V
I _{GSS} (Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V			±100	nA
R _{DS(ON)}	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =75A		3.2	4	mΩ
Diode Chara	acteristics					
V _{SD} ⁴	Diode Forward Voltage	I _{SD} =75A, V _{GS} =0V			1.2	V
	Reverse Recovery Time	175A dl/dt-100A/vo		36		ns
Qrr F	Reverse Recovery Charge	IsD=75A, dlsD/dt=100A/μs		28		nC
Dynamic Ch	naracteristics ^⑤					
R _G (Gate Resistance	V_{GS} =0V, V_{DS} =0V,F=1MHz		2.1		Ω
C _{iss} I	Input Capacitance	V _{GS} =0V,		3650		
Coss	Output Capacitance	V _{DS} =50V, Frequency=1.0MHz		750		pF
C _{rss} F	Reverse Transfer Capacitance	Troquonoy 1.0MHZ		27		
t _{d(ON)}	Turn-on Delay Time			24		
t _r 7	Turn-on Rise Time	V _{DD} =50V,I _{DS} =75A,		13		no
t _{d(OFF)}	Turn-off Delay Time	V_{GEN} =10V, R_{G} =2.5 Ω		49		ns
t _f 7	Turn-off Fall Time			17		
Gate Charge	e Characteristics ^⑤					
1	Total Gate Charge			87		
Q _{gs} (Gate-Source Charge	V _{DS} =80V, V _{GS} =10V, I _{DS} =75A		23		nC
	Gate-Drain Charge	IDS 1 OA		15		

Notes:

①Pulse width limited by safe operating area.

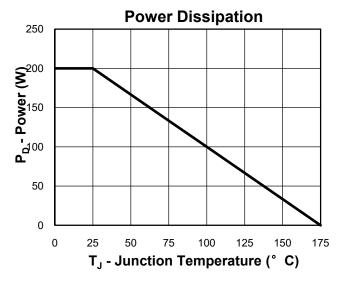
②Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.

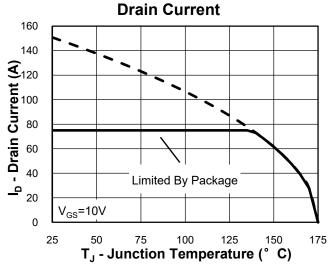
[⊕]Pulse test;Pulse width $≤300\mu s$, duty cycle≤2%.

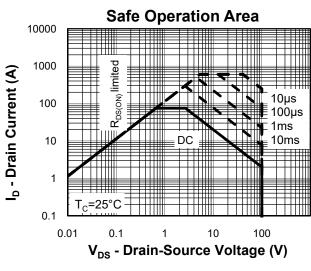
⑤Guaranteed by design, not subject to production testing.

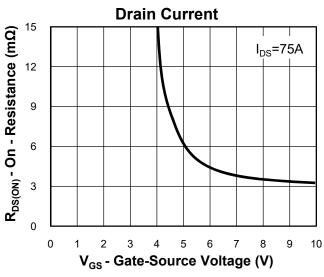


Typical Characteristics

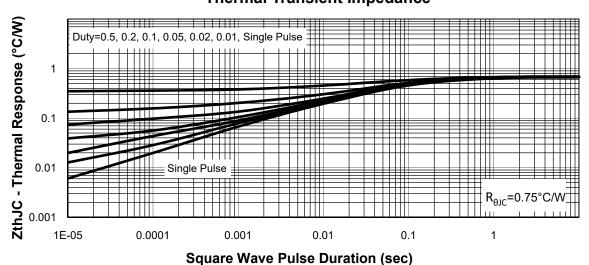






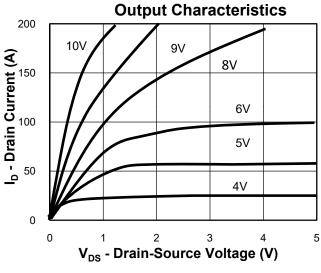


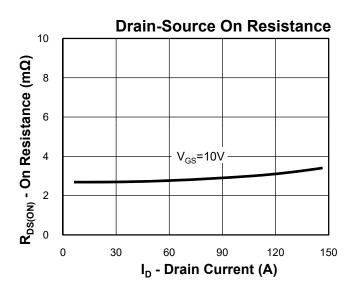
Thermal Transient Impedance

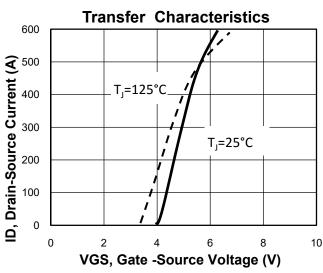


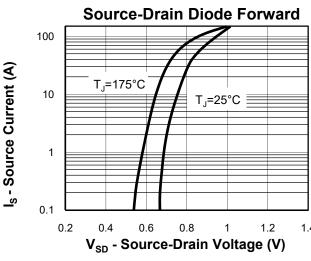


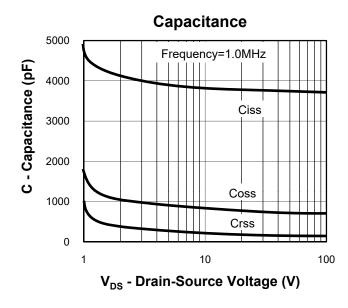
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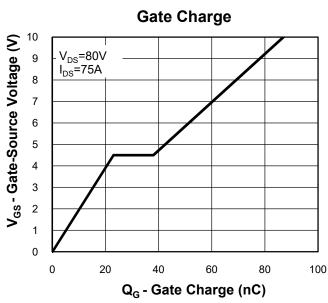






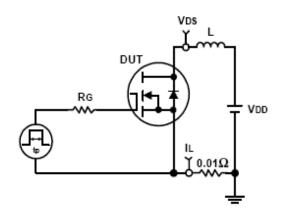


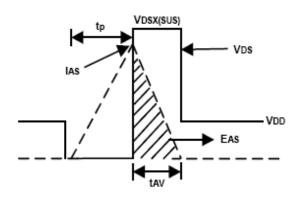




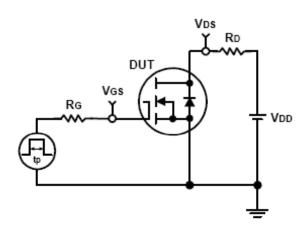


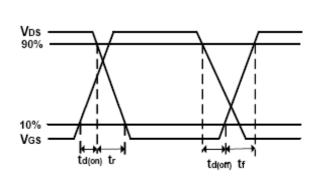
Avalanche Test Circuit and Waveforms





Switching Time Test Circuit and Waveforms





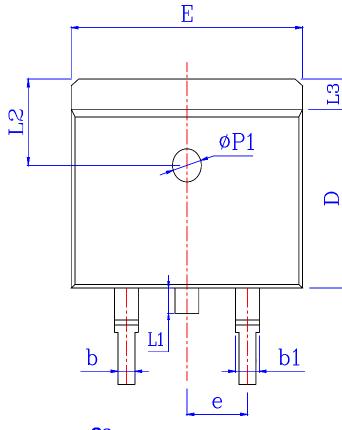
Ordering and Marking Information

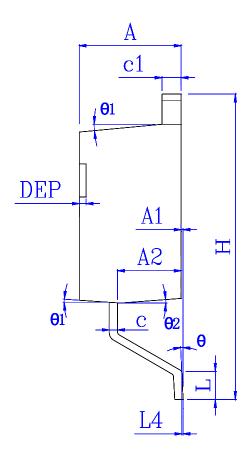
Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
XPX0115TU	XPX0115TU	TO263	Tube	50	-	-
XPX0115TU-R	XPX0115TU	TO263	Tape&Reel	800	13"	24mm

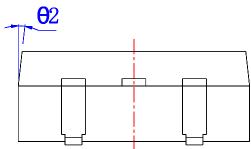


Package Information

TO263





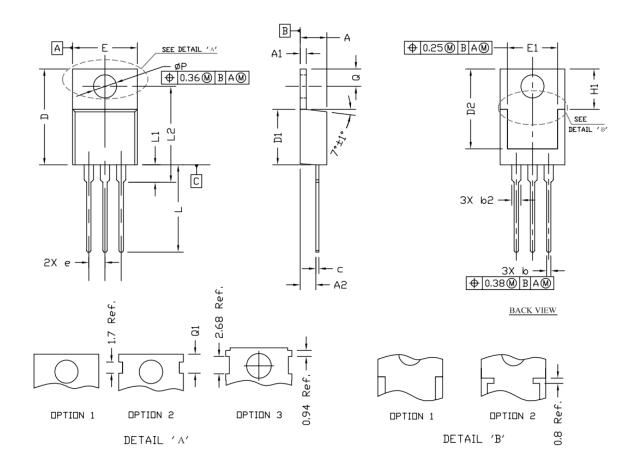


SYMBOL		MM			INCH		SYMBOL		MM			INCH	
OIMDOL	MIN	NOM	MAX	MIN	NOM	MAX	OIMDOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.55	4.85	0.169	0.179	0.191	L	1.94	2.30	2.79	0.076	0.091	0.110
A1	0.00	0.10	0.25	0.000	0.005	0.010	L3	1.02	1.29	1.40	0.040	0.051	0.055
A2	2.20	2.69	2.79	0.087	0.106	0.110	L1	*	*	1.70	*	*	0.067
b	0.70	*	1.00	0.028	*	0.039	L4		0.25 BSC			0.01 BSC	
b1	1.14	*	1.47	0.045	*	0.058	L2		2.50 REF			0.098 REF	ì
С	0.33	*	0.65	0.013	*	0.026	θ	0°	*	8°	0°	*	8°
c1	1.15	*	1.45	0.045	*	0.057	θ1	5°	7°	9°	5°	7°	9°
D	8.59	*	9.40	0.338	*	0.370	θ2	1°	3°	5°	1°	3°	5°
E	9.66	*	10.40	0.380	*	0.409	DEP	0.05	0.10	0.20	0.002	0.004	0.008
е		2.54BSC			0.100BSC		Фр1	1.40	1.50	1.60	0.055	0.059	0.063
Н	14.70	15. 10	15.79	0.579	0.594	0.622							

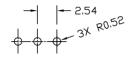


Package Information

TO220 PACKAGE OUTLINE



RECOMMENDATION OF HOLE PATTERN



UNIT: mm

- NOTE

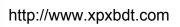
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 MOLD FLASH SHOULD BE LESS THAN 6 MIL.

 2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.

 3. CONTROLLING DIMENSION IS MILLIMETER.

- CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

	DIMENS	IONS IN MILI	LIMETERS	DIMENSIONS IN INCHES				
SYMBOLS	MIN	NDM	MAX	MIN	NDM	MAX		
Α	4.30	4,45	4.72	0,169	0,175	0.186		
A1	1.15	1.27	1.40	0.045	0.050	0.055		
A2	2.20	2.67	2.90	0.087	0,105	0.114		
b	0.69	0.81	0.95	0.027	0.032	0.037		
b2	1.17	1.37	1.45	0.046	0.050	0.068		
C	0.36	0.38	0.60	0.014	0.015	0.024		
D	14.50	15,44	15.80	0.571	0.608	0.622		
D1	8.59	9.14	9,65	0.338	0.360	0.380		
D2	11.43	11.73	12.48	0.450	0.462	0.491		
е		2.54 BS0			0.100 BSC	100 BSC.		
E	9.66	10.03	10.54	0.380	0,395	0,415		
E1	6.22			0.245				
H1	6.10	6.30	6.50	0.240	0.248	0.256		
L	12.27	12.82	14.27	0.483	0.505	0.562		
L1	2.47		3,90	0.097		0.154		
L2			16.70			0.657		
Q	2.59	2.74	2.89	0.102	0.108	0.114		
ØΡ	3.50	3.84	3,89	0.138	0.151	0.153		
Q1	2.70		2.90	0.106		0.114		





Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245 ℃ ±5 ℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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